Quad 3-state Buffer with Low Enable

High-Performance Silicon-Gate CMOS

Features

- Outputs Source/Sink
- 'ACT125 Has TTL Compatible Inputs
- These are Pb-Free Devices

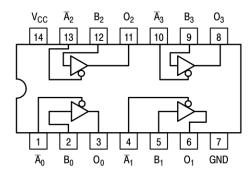


Figure 1. Pinout: 14-Lead Packages Conductors (Top View)

PIN ASSIGNMENT

PIN	FUNCTION
\overline{A}_n , B_n	Inputs
O _n	Outputs

FUNCTION TABLE

Inp	uts	Output
\overline{A}_n	B _n	O _n
L	L	L
l L	H X	H Z

NOTE: H = High Voltage Level;

L = Low Voltage Level; Z = High Impedance;

X = Immaterial

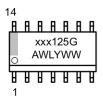


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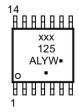


SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



xxx = AC or ACT

A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		$-0.5 \leq V_I \leq V_{CC} + 0.5$	V
Vo	DC Output Voltage	(Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current		± 20	mA
lok	DC Output Diode Current		± 50	mA
Io	DC Output Sink/Source Current		± 50	mA
I _{CC}	DC Supply Current per Output Pin		± 50	mA
I _{GND}	DC Ground Current per Output Pin		± 50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Second	ds	260	°C
TJ	Junction temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	125 170	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxyg	en Index: 30% - 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	Ma	Body Model (Note 3) achine Model (Note 4) Device Model (Note 5)	> 2000 > 200 > 1000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below 0	GND at 85°C (Note 6)	± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- I_O absolute maximum rating must be observed.
 The package thermal impedance is calculated in accordance with JESD51-7.
 Tested to EIA/JESD22-A114-A.
- 4. Tested to EIA/JESD22-A115-A.
- Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
	0 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1	'AC	2.0	5.0	6.0	.,
V_{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Ref. to GND)		0	-	V _{CC}	V
	t _r , t _f Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 3.0 V	-	150	-	
t_r, t_f		V _{CC} @ 4.5 V	-	40	-	ns/V
	The Berness shoops commit impais	V _{CC} @ 5.5 V	-	25	-	
TJ	Junction Temperature (PDIP)		-	-	140	°C
T _A	Operating Ambient Temperature Range		-40	25	85	°C
I _{OH}	Output Current - HIGH		-	-	-24	mA
l _{OL}	Output Current - LOW		-	-	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. V_{in} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.

2. V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

	Parameter		74AC		74AC			
Symbol		V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions	
			Тур	Guara	anteed Limits]		
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.46 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = - 50 μA	
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ -12 mA I_{OH} -24 mA -24 mA	
V _{OL}	Minimum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	I _{OUT} = 50 μA	
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ 12 mA I_{OL} 24 mA 24 mA	
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μА	V _I = V _{CC} , GND	
l _{OZ}	V_I (OE) = V_{IL} , V_{IH} V_I = V_{CC} , GND V_O = V_{CC} , GND	5.5	-	±0.5	±5.0	μΑ	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND	
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}	Output Current	5.5	-	_	-75	mA	V _{OHD} = 3.85 V Min	
I _{CC}	Maximum Quiescent Supply Current	5.5	_	8.0	80	μΑ	$V_{IN} = V_{CC}$ or GND	

^{*}All outputs loaded; thresholds on input associated with output under test.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V.

AC CHARACTERISTICS

			74	AC	74AC		
Symbol	Parameter	V _{CC} * (V)	T _A = +25°C C _L = 50 pF		T _A = -40°C to +85°C C _L = 50 pF		Unit
			Min	Max	Min	Max	
t _{PLH}	Propagation Delay Data to Output	3.3 5.0	1.0 1.0	9.0 7.0	1.0 1.0	10 7.5	ns
t _{PHL}	Propagation Delay Data to Output	3.3 5.0	1.0 1.0	9.0 7.0	1.0 1.0	10 7.5	ns
t _{PZH}	Output Enable Time	3.3 5.0	1.0 1.0	10.5 7.0	1.0 1.0	11 8.0	ns
t _{PZL}	Output Enable Time	3.3 5.0	1.0 1.0	10 8.0	1.0 1.0	11 8.5	ns
t _{PHZ}	Output Disable Time	3.3 5.0	1.0 1.0	10 9.0	1.0 1.0	10.5 9.5	ns
t _{PLZ}	Output Disable Time	3.3 5.0	1.0 1.0	10.5 9.0	1.0 1.0	11.5 9.5	ns

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. Voltage Range 5.0 V is 5.0 V ± 0.5 V.

[†]Maximum test duration 2.0 ms, one input loaded at a time.

DC CHARACTERISTICS

	Parameter		74ACT T _A = +25°C		74ACT		
Symbol		V _{CC} (V)			T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guara	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.2 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = - 50 μA
		4.5 5.5		3.86 4.86	3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ -24 mA $^{I}_{OH}$ -24 mA
V _{OL}	Minimum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = - 50 μA
		4.5 5.5		0.36 0.36	0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} - 24 \text{ mA}$ $- 24 \text{ mA}$
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V _I = V _{CC} , GND
l _{OZ}	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND	5.5	-	±0.5	±5.0	μΑ	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I _{OLD}	†Minimum Dynamic	5.5	_	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	-75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	_	8.0	80	μА	$V_{IN} = V_{CC}$ or GND

^{*}All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one input loaded at a time.

AC CHARACTERISTICS

			74ACT 74ACT		СТ		
Symbol	Parameter	V _{CC} *			T _A = -40°C to +85°C C _L = 50 pF		Unit
				Max	Min	Max	
t _{PLH}	Propagation Delay Data to Output	5.0	1.0	9.0	1.0	10	ns
t _{PHL}	Propagation Delay Data to Output	5.0	1.0	9.0	1.0	10	ns
t _{PZH}	Output Enable Time	5.0	1.0	8.5	1.0	9.5	ns
t _{PZL}	Output Enable Time	5.0	1.0	9.5	1.0	10.5	ns
t _{PHZ}	Output Disable Time	5.0	1.0	9.5	1.0	10.5	ns
t _{PLZ}	Output Disable Time	5.0	1.0	10	1.0	10.5	ns

^{*}Voltage Range 5.0 V is 5.0 V ±0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	45	pF	V _{CC} = 5.0 V

ORDERING INFORMATION

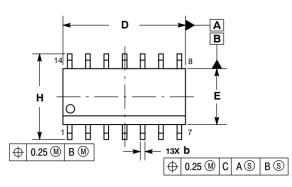
Device	Package	Shipping [†]
MC74AC125DG	SOIC-14	55 Units / Rail
MC74AC125DR2G	(Pb-Free)	2500 / Tape & Reel
MC74AC125DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74ACT125DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74ACT125DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

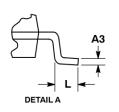
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

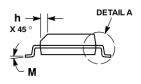


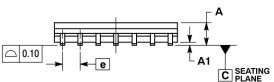
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









SOLDERING FOOTPRINT*

MIN MAX MIN MAX Α 0.054 0.068 A1 0.10 0.25 0.004 0.010 0.25 0.008 0.010 A3 0.19 0.35 0.49 0.014 b 8.55 8.75 0.337 0.344 3.80 4.00 0.150 0.157 D E 1.27 BSC 0.050 BSC e H 6.20 0.228 h 0.25 0.50 0.010 0.019 0.40 1.25 0.016 0.049

NOTES:
1. DIMENSIONING AND TOLERANCING PER

MAXIMUM MATERIAL CONDITION.

DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

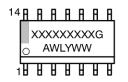
MILLIMETERS

5. MAXIMUM MOLD PROTRUSION 0.15 PER

ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT

GENERIC MARKING DIAGRAM*

INCHES



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ", may or may not be present.

6.50 14X 1.18 1.18 1.27 PITCH

DIMENSIONS: MILLIMETERS

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

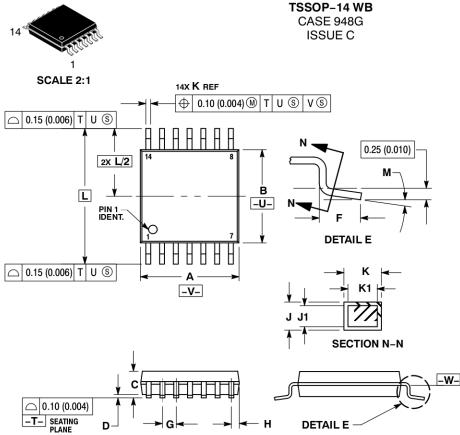
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 DIMENSION B DOES NOT INCLUDE
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- INTERLEAD FLASH OR PROTHUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
м	o°	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

(Note: Microdot may be in either location)

SOLDERING	FOOTPRINT
7.	06 —
1	
	0.65 PITCH
↓	——————————————————————————————————————
0.36 14X 1.26	I DIMENSIONS: MILLIMETERS

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